

Quad Programmable Bipolar JFET Operational Amplifier

GENERAL DESCRIPTION

The XR-096 monolithic circuit contains four independently programmable JFET operational amplifiers in a single IC package. Each of the four op amp sections on the chip has its own external bias terminal; thus its performance characteristics and power dissipation can be independently controlled, without effecting the other op amp sections on the chip. The respective bias-setting resisters, RSET, connected to the programming terminals of the circuit allow one to trade-off power dissipation for slew-rate, without sacrificing the gain-bandwidth product of the circuit. These individual bias terminals can also be used to switch the op amp sections "on" and "off", and thus, multiplex between various op amp channels on the same chip.

FEATURES

Programmable Version of XR-084
Independent Programming of All Four Op Amps
Programmable for Micropower Operation
High-Impedance JFET Input Stage
Internal Frequency Compensation
Low Input Bias and Offset Currents

APPLICATIONS

Supply Voltage

Total Supply Current = 5.6 mA (I_{SET}/320 μ A) Slew-Rate = 13 V/ μ s (I_{SET}/320 μ A) I_{SET} = Current into set terminal

$$I_{SET} = \frac{V_{CC} - (V_{EE} - 0.6V)}{R_{SET}}$$

Note. ISFT must be ≤ 400µA

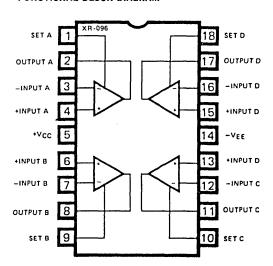
ABSOLUTE MAXIMUM RATINGS

Differential Input Voltage	± 30V
Input Voltage Range (Note 1)	± 15V
Output Short-Circuit Duration (Note	2) Indefinite
Package Power Dissipation:	,
Plastic Package	625 mW
Derate Above T _A = +25°C	5.0 mV/°C
Ceramic Package	750 mW
Derate Above T _A = +25°C	6.0 mW/°C
Storage Temperature Range	-65°C to +150°C

Note 1: For Supply Voltage less than ±15V, the absolute maximum input voltage is equal to the supply voltage.

Note 2: The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

FUNCTIONAL BLOCK DIAGRAM



ORDERING INFORMATION

Package	Operating Temperature
Ceramic	-25°C to +85°C
Plastic	-25°C to +85°C
Ceramic	0°C to +70°C
Plastic	0°C to +70°C
	Ceramic Plastic Ceramic

SYSTEM DESCRIPTION

The XR-096 is a quad independently programmable JFET input operational amplifier featuring extremely high input resistance, low input bias and offset current, large common mode voltage range, and large output swing range. Unity gain bandwidth is 3 MHz, and slew rate is $13VI_{\mu}S$. The devices are unity gain compensated.

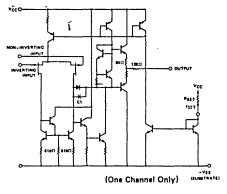
Each of the form amplifiers may be independently "programmed"-rebiased-by connecting a resistor from the bias adjust pin to the positive supply. Bias current may range up to 400 μ A, thus affording the designer flexibility along the power consumption/speed curve.

 $\pm 18V$

ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}\text{C}$, $V_{CC} = \pm 15\text{V}$, unless otherwise specified. ISET = 320 μA .

		XR-09	6	XR-096C					
PARAMETERS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS	SYMBOL	CONDITIONS
Input Offset Voltage		3	6 9		5	15 20	mV mV	V _{OS} V _{OS}	$R_S = 50\Omega$, $T_A = 25$ °C $R_S = 50\Omega$, $T_A = Full Range$
Offset Voltage Temp. Coef.		10			10		μV/°C	ΔV _{OS} /ΔΤ	$R_S = 50\Omega$, $T_A = Full Range$
Input Bias Current		80	600 20		80	800 20	pA nA	lΒ	T _A = 25°C T _A = Full Range
Input Offset Current		40	300 10		40	500 5	pA nA	los	T _A = 25°C T _A = Full Range
Supply Current (per amplifier)		1.4	2.8		1.4	2.8	mA	lcc	No Load, No Input Signal
Input Common Mode Range	± 12			±10			٧	V _{iCM}	
Voltage Gain	50 25	200		25 15	200		V/mV	Avol	$R_L \ge 2K\Omega$, $V_0 = \pm 10V$ $T_A = 25^{\circ}C$ $T_A = Full Range$
Max. Output Swing (peak-to-peak)	24 24	27		24 24	27		V	V _{OPP}	R _L ≥ 10 KΩ T _A = 25°C T _A = Full Range
Input Resistance		1012			1012		Ω	R _{in}	T _A = 25°C
Unity-Gain Bandwidth		3			3		MHz	BW	T _A = 25°C
Common-Mode Rejection	80	86		70	76		dB	CMRR	$R_{S} \leq 10 \text{ K}\Omega$
Supply-Voltage Rejection	80	86		70	76		dB	PSRR	
Channel Separation		120			120		dB		Ay 100, Freq. = 1 kHz
Slew Rate		13			13		V/μS	dV _{out/dt}	$A_V = 1$, $R_L = 2 K\Omega$ $C_L = 100 pF$, $V_1 = 10V$
Rise Time Overshoot		0.1 10			0.1 10		μsec %	t _r t _o	$A_V = 1$, $R_L = 2 K\Omega$ $C_L = 100 pF$, $V_1 = 20 mV$
Equivalent Input Noise Voltage		18			18		nV/√Hz	e _n	$R_{S} = 100\Omega$ $f = 1 \text{ kHz}$



EQUIVALENT SCHEMATIC DIAGRAM